DIGITRON SEMICONDUCTORS

MFE211 – MFE212

N-CHANNEL DUAL GATE SILICON NITRIDE PASSIVATED MOS FIELD EFFECT TRANSISTORS

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain Source Voltage	V_{DSX}	20	Vdc
Drain Gate Voltage	V_{DG1} V_{DG2}	35 35	Vdc
Gate Current	I_{G1} I_{G2}	±10 ±10	mAdc
Drain Current – Continuous	I_D	50	mAdc
Total Power Dissipation @ T_A = 25°C **Derate above 25°C**	P_D	360 2.4	mW mW/°C
Total Power Dissipation @ T_C = 25°C **Derate above 25°C**	P_D	1.2 8.0	Watt mW/°C
Storage Channel Temperature Range	T_{stg}	-65 to +200	°C
Junction Temperature Range	T_J	-65 to +175	°C
Lead Temperature, 1/16" from Seated Surface for 10 Seconds	T_L	300	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristics		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Drain Source Breakdown Voltage (I_D = 10 μAdc, V_{G1S} = V_{G2S} = -4.0 Vdc)		$V_{(BR)DSX}$	20	-	Vdc
Gate 1 – Source Breakdown Voltage [(1)] (I_{G1} = ±10 mAdc, V_{G2S} = V_{DS} = 0)		$V_{(BR)G1SO}$	±6.0	-	Vdc
Gate 2 – Source Breakdown Voltage [(1)] (I_{G2} = ±10 mAdc, V_{G1S} = V_{DS} = 0)		$V_{(BR)G2SO}$	±6.0	-	Vdc
Gate 1 to Source Cutoff Voltage (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 20 μAdc)	MFE211 MFE212	$V_{G1S(off)}$	-0.5 -0.5	-5.5 -4.0	Vdc
Gate 2 to Source Cutoff Voltage (V_{DS} = 15 Vdc, V_{G1S} = 0, I_D = 20 μAdc)	MFE211 MFE212	$V_{G2S(off)}$	-0.2 -0.2	-2.5 -4.0	Vdc
Gate 1 Leakage Current (V_{G1S} = ±5.0 Vdc, V_{G2S} = V_{DS} = 0) (V_{G1S} = -5.0 Vdc, V_{G2S} = V_{DS} = 0, T_A = 150°C)		I_{G1SS}	- -	±10 -10	mAdc μAdc
Gate 2 Leakage Current (V_{G2S} = ±5.0 Vdc, V_{G1S} = V_{DS} = 0) (V_{G2S} = -5.0 Vdc, V_{G1S} = V_{DS} = 0, T_A = 150°C)		I_{G2SS}	- -	±10 -10	nAdc μAdc
ON CHARACTERISTICS					
Zero-Gate Voltage Drain Current [(2)] (V_{DS} = 15 Vdc, V_{G1S} = 0, V_{G2S} = 4.0 Vdc)		I_{DSS}	6.0	40	mAdc
SMALL SIGNAL CHARACTERISTICS					
Forward Transfer Admittance [(3)] (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, V_{G1S} = 0, f = 1.0 kHz)		$\|Y_{fs}\|$	17	40	mmhos
Reverse Transfer Capacitance (V_{DS} = 15 Vdc, V_{G2S} = 4.0 Vdc, I_D = 10 mAdc, f = 1.0 MHz)		C_{rss}	0.005	0.05	pF
FUNCTIONAL CHARACTERISTICS					
Noise Figure (V_{DD} = 18 Vdc, V_{GG} = 7.0 Vdc, f = 200 MHz) (V_{DD} = 24 Vdc, V_{GG} = 6.0 Vdc, f = 45 MHz)	MFE211 MFE212	NF	- -	3.5 4.0	dB
Common Source Power Gain (V_{DD} = 18 Vdc, V_{GG} = 7.0 Vdc, f = 200 MHz) (V_{DD} = 18 Vdc, V_{GG} = 6.0 Vdc, f = 45 MHz) (V_{DD} = 18 Vdc, f_{LO} = 245 MHz, f_{RF} = 200 MHz)	MFE211 MFE211 MFE212	G_{ps} G_c [(5)]	24 29 21	35 37 28	dB

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MFE211 – MFE212

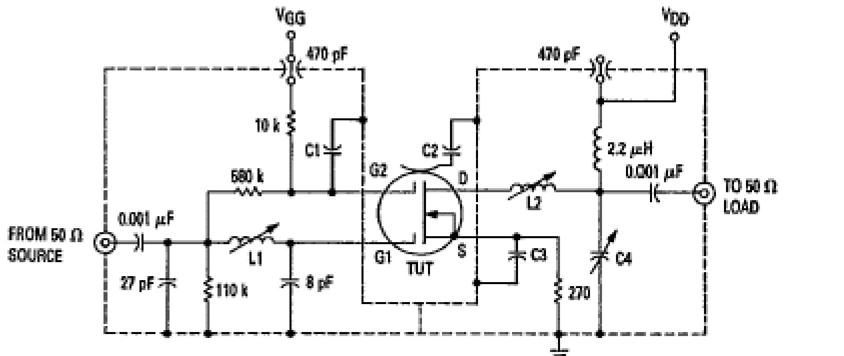
N-CHANNEL DUAL GATE SILICON NITRIDE PASSIVATED MOS FIELD EFFECT TRANSISTORS

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristics		Symbol	Min	Max	Unit
Bandwidth					
(V_{DD} = 18 Vdc, V_{GG} = 7.0 Vdc, f = 200 MHz)	MFE211	BW	5.0	12	MHz
(V_{DD} = 18 Vdc, f_{LO} = 245 MHz, f_{RF} = 200 MHz)	MFE212		4.0	7.0	
(V_{DD} = 18 Vdc, V_{GG} = 6.0 Vdc, f = 45 MHz)	MFE211		3.5	6.0	
Gain Control Gate Supply Voltage [(4)]					
(V_{DD} = 18 Vdc, ΔG_{ps} = -30 dB, f = 200 MHz)	MFE211	$V_{GG(GC)}$	-	-2.0	Vdc
(V_{DD} = 18 Vdc, ΔG_{ps} = -30 dB, f = 45 MHz)	MFE211		-	±1.0	

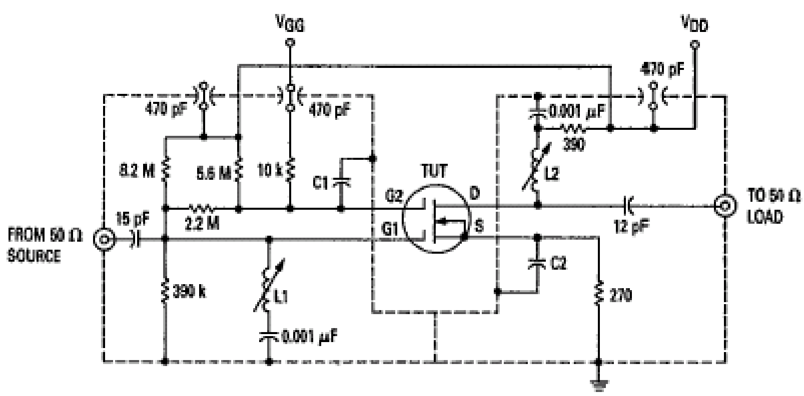
1. All gate breakdown voltages are measured while the device is conducting rated gate current. This ensures that the gate voltage limiting network is functioning properly.
2. Pulse test: Pulse width = 300μs, duty cycle ≤ 2%.
3. This parameter must be measured with bias voltages applied for less than 5 seconds to avoid overheating. The signal is applied to gate 1 with gate 2 at ac ground.
4. ΔG_{ps} is defined as the change in G_{ps} from the value at V_{GG} = 7.0 volts (MFE211).
5. Power Gain Conversion. Amplitude at input from local oscillator is adjusted for maximum G_C.

Available Non-RoHS (standard) or RoHS compliant (add PBF suffix).
Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.



C1, C2 & C3: Leadless disc ceramic, 0.001 µF
C4: ARCO 462, 5–80 pF, or equivalent
L1: 3 Turns #18, 3/16" diameter aluminum slug
L2: 8 Turns #20, 3/16" diameter aluminum slug

Figure 1. 200 MHz Power Gain, Gain Control Voltage, and Noise Figure Test Circuit for MFE211



C1: Leadless disc ceramic, 0.001 µF
C2: Leadless disc ceramic, 0.01 µF
L1: 8 Turns #28, 5/32" diameter form, type "J" slug
L2: 9 Turns #28, 5/32" diameter form, type "J" slug

Figure 2. 45 MHz Power Gain and Noise Figure Test Circuit for MFE211

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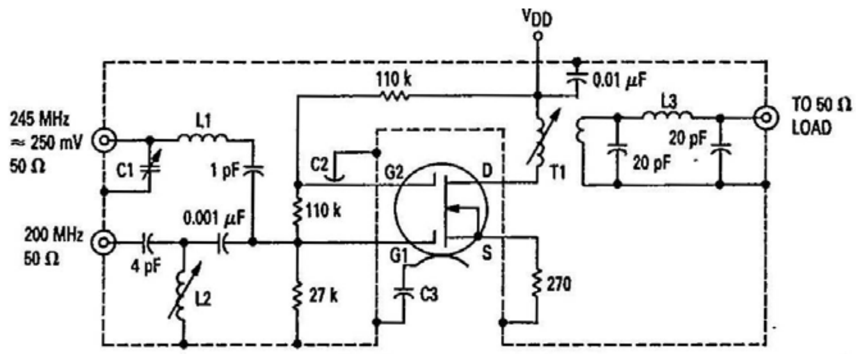


L1: 7 Turns #34, 1/4" diameter aluminum slug
L2: 5-1/2 Turns #20, 1/4" diameter aluminum slug
L3: 7 Turns #24, 1/4" diameter air core

C1: Arco type 462, 5–80 pF
C2: 0.001 μF leadless disc
C3: 0.01 μF leadless disc

T1: Pri: 25 Turns #30, close wound on 1/4" diameter form, type "J" slug
Sec: 4 Turns #30, centered over primary

Figure 3. 200 MHz-to-45 MHz Circuit for Conversion Power Gain for MFE212

TYPICAL CHARACTERISTICS

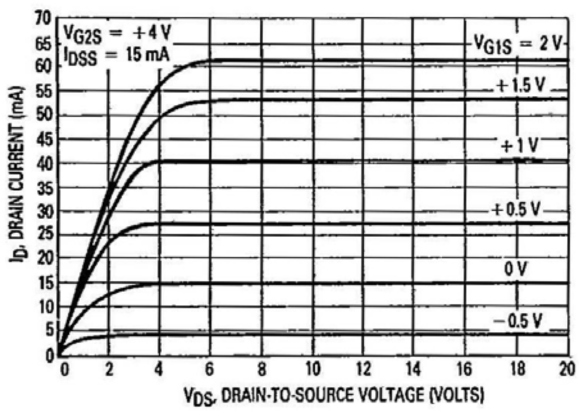


Figure 4. Drain Current versus Drain-to-Source Voltage

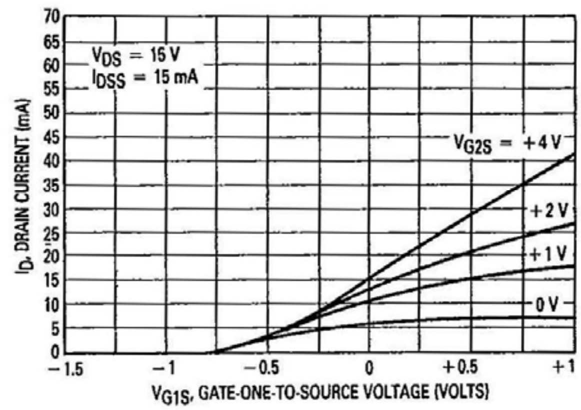


Figure 5. Drain Current versus Gate-One-to-Source Voltage

SMALL-SIGNAL COMMON-SOURCE PARAMETER

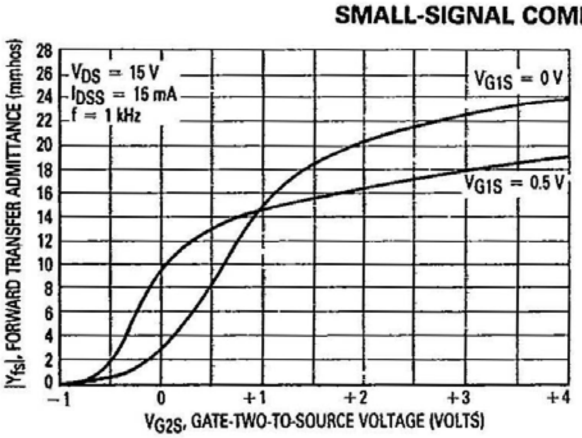


Figure 6. Forward Transfer Admittance versus Gate-Two-to-Source Voltage

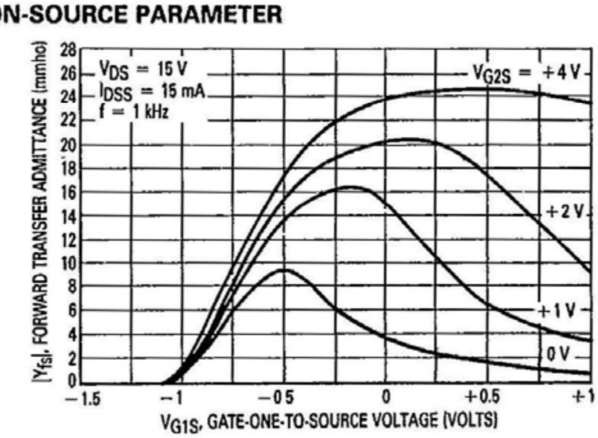


Figure 7. Forward Transfer Admittance versus Gate-One-to-Source Voltage

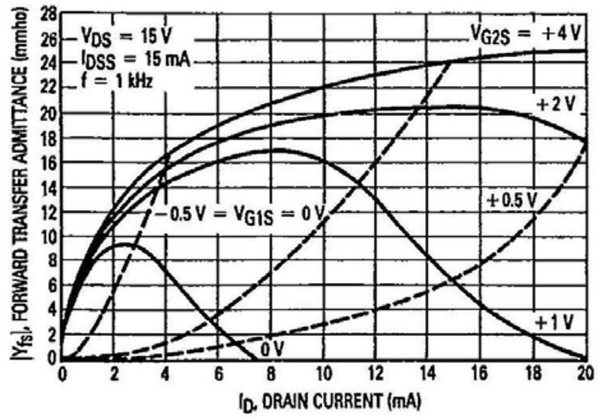


Figure 8. Forward Transfer Admittance versus Drain Current

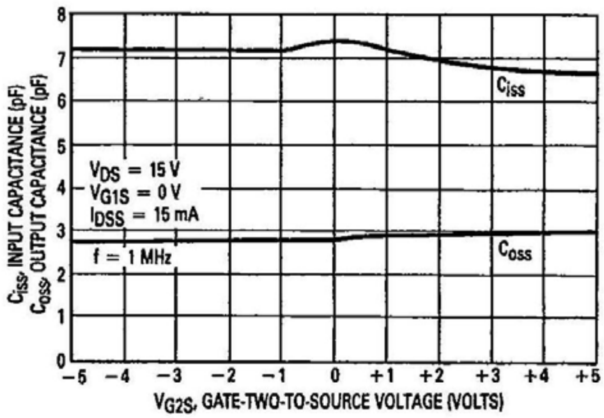


Figure 9. Input and Output Capacitance versus Gate-Two-to-Source Voltage

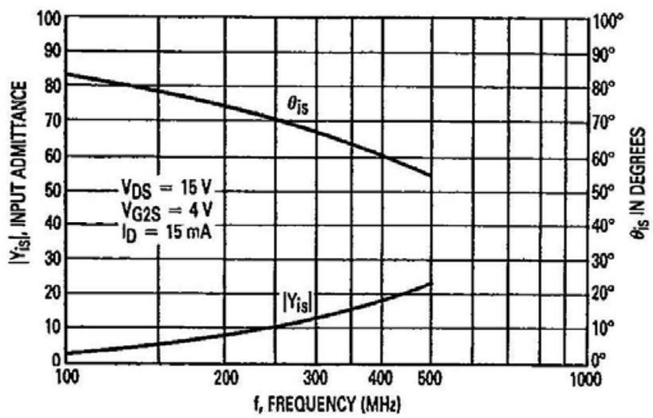


Figure 10. Small-Signal Gate-One Input Admittance versus Frequency

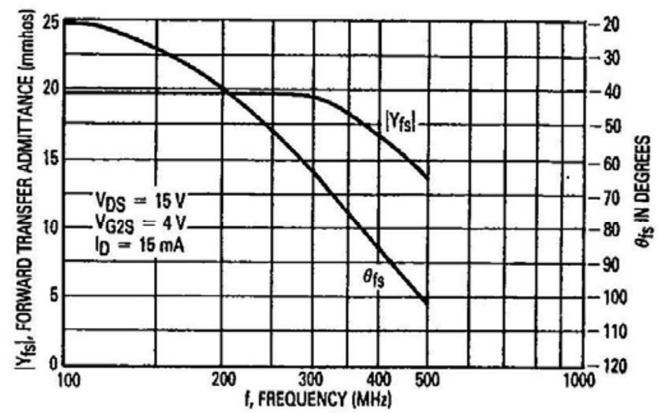


Figure 11. Small-Signal Forward Transfer Admittance versus Frequency

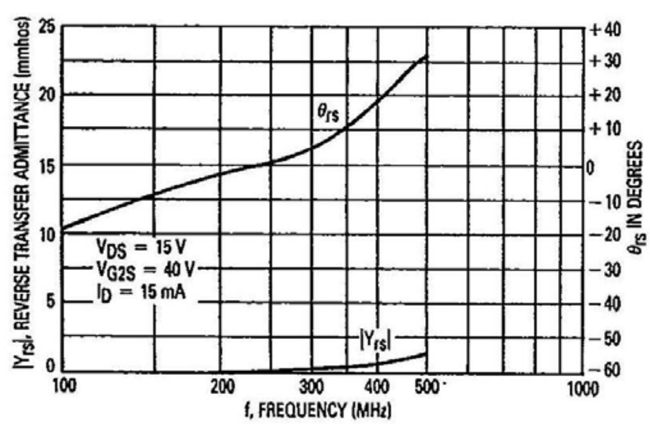


Figure 12. Small-Signal Gate-One Reverse Transfer Admittance versus Frequency

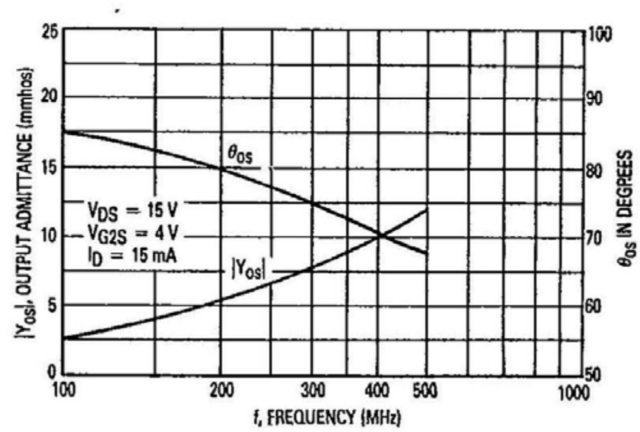


Figure 13. Small-Signal Gate-One Output Admittance versus Frequency

MFE211 – MFE212

N-CHANNEL DUAL GATE SILICON NITRIDE PASSIVATED MOS FIELD EFFECT TRANSISTORS

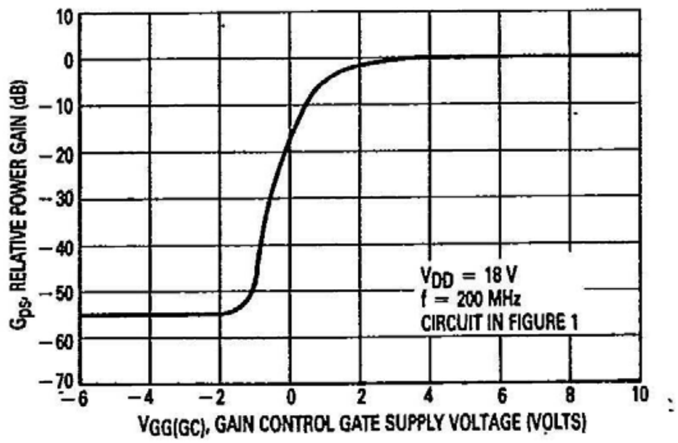


Figure 14. Relative Small-Signal Power Gain versus Gain Control Gate Supply Voltage MFE211

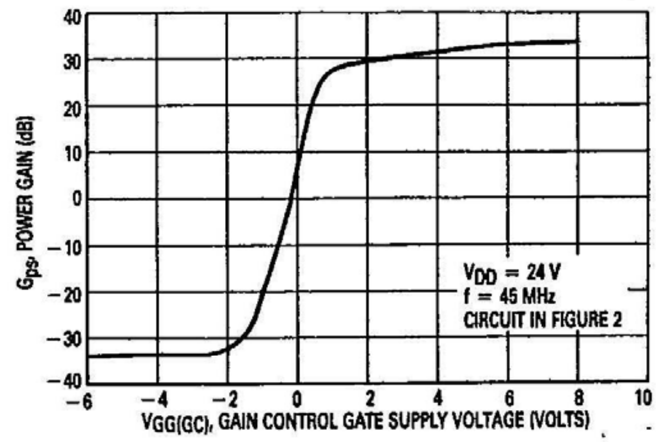


Figure 15. Small-Signal Common-Source Insertion Power Gain versus Gain Control Gate Supply Voltage

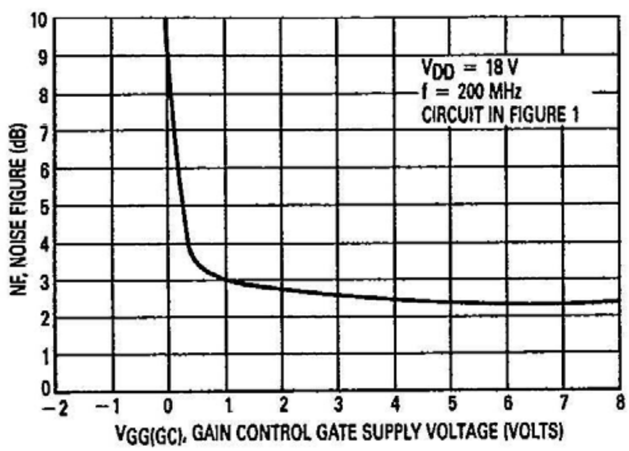


Figure 16. Common Source Spot Noise Figure versus Gain Control Gate Supply Voltage

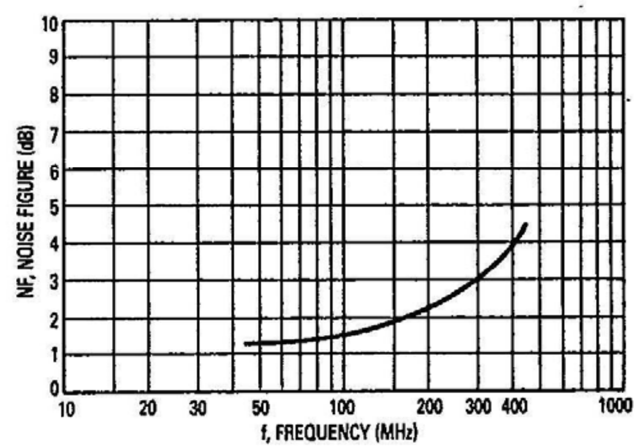
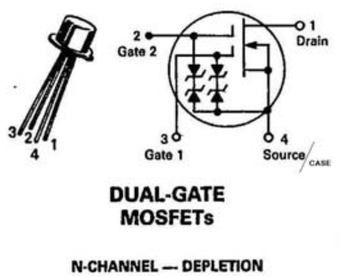
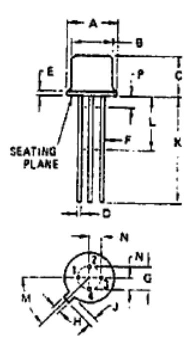


Figure 17. Optimum Spot Noise Figure versus Frequency

TO-72





Dim	Inches		Millimeters	
	Min	Max	Min	Max
A	-	0.230	-	5.840
B	-	0.195	-	4.950
C	-	0.210	-	5.330
D	-	0.021	-	0.530
E	-	0.030	-	0.760
F	-	0.019	-	0.480
G	0.100 BSC		2.540 BSC	
H	-	0.046	-	1.170
J	-	0.0480	-	1.220
K	0.500	-	12.700	-
L	0.250	-	6.350	-
M	45°C BSC		45°C BSC	
N	0.050 BSC		1.270 BSC	
P	-	0.050	-	1.270